

<p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> <p style="text-align: center;">JAN 03 2005 PATENT & TRADEMARK OFFICE U.S. DEPARTMENT OF COMMERCE</p>				Docket Number (Optional) BREV 12370 CON4		Application Number 10/784,601	
				Applicant(s) ASPAR et al.			
				Filing Date February 23, 2004		Group Art Unit 2812 2823	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
G		SU 1282757	12.30.83	RUSSIA	H01L	21/265	
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER				DATE CONSIDERED		9/17/05	
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G		Reissue App. 10/449,786					
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
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*EXAMINER INITIAL G	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
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	"Orientation Dependence of Flaking of Ion Irradiated Aluminum Single Crystals" Ono et al., <i>Japanese Journal of Applied Physics</i> , Volume 25, No., 10, 1986, pgs. 1475-1480		
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INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

BREV 12370

N3

Application Number

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Applicant(s)

ASPAR et al

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February 6, 2001

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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)		Application Number
BREV 12370		09/777,516
Applicant(s)		Group Art Unit
ASPAR et al.		
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Applicant(s) ASPAR et al.		Group Art Unit 2823
Filing Date February 6, 2001		

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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

BREV 12370

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Docket Number (Optional)		Application Number
BREV 12370 (X3)		09/777,516
Applicant(s)		COPY
ASPAR, et al.		
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February 6, 2001		2823

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G	Stephan, D., "Investigation of Lattice Strain in Proton-Irradiated GaP by a Modified Auleytner Technique" phys. stat. sol. (a) 87, pp. 589-96 (1985).
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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

BREV 12370

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ASPAR ET AL

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
DK G	4,704,302	11/3/87	Bruel et al			
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↓ G	5,250,446	10/5/93	Osowa et al			

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						YES	NO
DK G	WO95/20824	8/3/95	PCT			✓	
	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
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DK G	EerNisse, E.P. et al, "Role of integrated lateral stress in surface deformation of He-implanted surfaces," Journal of Applied Physics, Vol 48, No 1, January 1997, pp 9-17
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INFORMATION DISCLOSURE STATEMENT
(Use several sheets if necessary)Docket Number (Optional)
BREV 12370 CON

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Aspar et al

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D. M. F.	Roth, J., "Blistering and bubble formation," Inst. Phys. Conf. Ser., No. 28, 1976, pp 280-293
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12-21-01 9/17/05

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~~D. M. Corvis~~ Fourson

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FORM PTO-1449	SERIAL NO. 10/784601	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE	GROUP ART UNIT 2823
	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

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<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Bruel et al.

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<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
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0355913	EPO	February 28, 1990
0504714	EPO	September 23, 1992

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FORM PTO-1449	SERIAL NO.	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT
(use several sheets if necessary)	APPLICANT(S):	Aspar et al.

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
Dale G	A1	4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
ES	A2	5,110,748	5/5/92	Sarma	437/51	7/22/91
CF	A3	5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
CF	A4	5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5					
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES	NO	
DAG	A9 2725074	3/29/96	France			X	
EG	A10 0355913	2/28/90	EPO		X		
EM	A11 0504714	9/23/92	EPO		X		

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DGC	A12	<u>Silicon-On-Insulator, European Semiconductor</u> , March, 1997, pages 17 and 18
G	A13	Aspar et al., <u>SMART-CUT & The basic fabrication process for UNIBOND & SOI wafers, SEMI 1996</u> , pp. 37-46
G	A14	<u>Klemi et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, Inst. Phys. Conf., Ser. No 96: Chapter 6, pp. 387-392</u>
G	A15	<u>Hamaguchi et al., Device Layer Transfer Technique using Chemi-Mechanical Polishing, Japanese Journal of Applied Physics, 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817</u>
G	A16	<u>Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations, Japanese Journal of Applied Physics, 28(1989), Aug., No. 8, Part 1, Tokyo, Japan, pp. 1426-1443</u>

EXAMINER *Dr. S. S. Fife Jr.* DATE CONSIDERED

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INFORMATION DISCLOSURE **SECTION**
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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANS. AT 21	
						YES	NO
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Daref	59-54217	03/29/1984	JAPAN	H01L	21/20		✓

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DAN G		WILLIAM PRIMAK ET AL IMPURITY EFFECT IN THE IONIZATION DILATATION OF VITREOUS SILICA 1967

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D.M. ~~CONTTS~~ Fourson

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BREV 12370 COX 2

Applicant(s)
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Group A

COPY

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